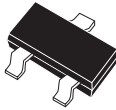


**CBAS17**

**LOW VOLTAGE STABISTOR**



**SOT-23 CASE**

**DESCRIPTION:**

The CENTRAL SEMICONDUCTOR CBAS17 type is a planar epitaxial silicon switching diode, designed for low voltage stabilizing applications.

**Marking code is A91.**

**MAXIMUM RATINGS** ( $T_A=25^{\circ}\text{C}$ )

	<b>SYMBOL</b>		<b>UNITS</b>
Peak Repetitive Forward Current	$I_{FRM}$	250	mA
Power Dissipation	$P_D$	350	mW
Operating and Storage			
Junction Temperature	$T_J, T_{stg}$	-65 to +150	$^{\circ}\text{C}$
Thermal Resistance	$\Theta_{JA}$	357	$^{\circ}\text{C}/\text{W}$

**ELECTRICAL CHARACTERISTICS** ( $T_A=25^{\circ}\text{C}$  unless otherwise noted)

<b>SYMBOL</b>	<b>TEST CONDITIONS</b>	<b>MIN</b>	<b>TYP</b>	<b>MAX</b>	<b>UNITS</b>
$V_F$	$I_F=0.1\text{mA}$	.580	.665	.680	V
$V_F$	$I_F=1.0\text{mA}$	.665	.745	.760	V
$V_F$	$I_F=5.0\text{mA}$	.725	.805	.820	V
$V_F$	$I_F=10\text{mA}$	.750	.825	.840	V
$V_F$	$I_F=100\text{mA}$	.870	.920	.960	V
$I_R$	$V_R=4.0\text{V}$			5.0	$\mu\text{A}$
$C_T$	$V_R=0, f=1\text{ MHz}$			140	pF

All dimensions in inches (mm).

